

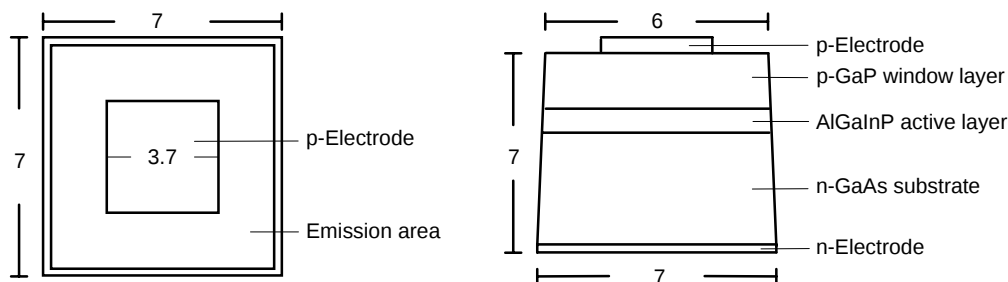
■ Features :

- HP MOVPE epi wafer
- Low VF and superior thermal stability
- Good for low current applications
- High light output at four sides results high total light output and good brightness uniformity
- Suitable for small and thin package
- High reliability

■ Typical Applications :

- SMD Chip LED
- Backlight
- Lamp Display

■ Outline Dimensions : (Unit: mil)



■ Physical Structure :

Chip dimension	Chip size	7.0 mils x 7.0 mils
	Thickness	7.0 mils
	Emission area	6.0 mils
	Bonding pad	3.7 mils
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	2.05	2.40	V
Reverse Voltage	V_R	$I_R = 10 \mu\text{A}$	5	-	-	V
Wavelength	λ_D	$I_F = 20 \text{ mA}$	-	590	-	nm
	Hue		576	586	596	
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	18	-	nm
Luminous Intensity	I_v	A1	15	-	-	mcd
		B1	25	-	-	
		C1	35	-	-	

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

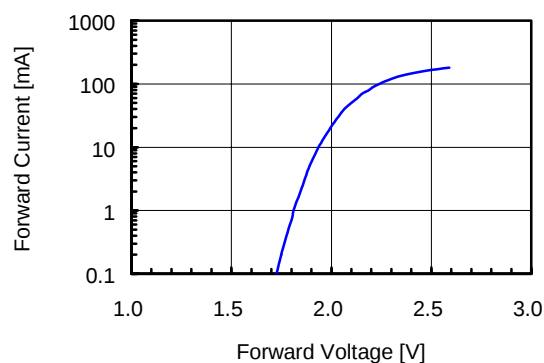


Fig 2. Relative Intensity vs. Forward Current

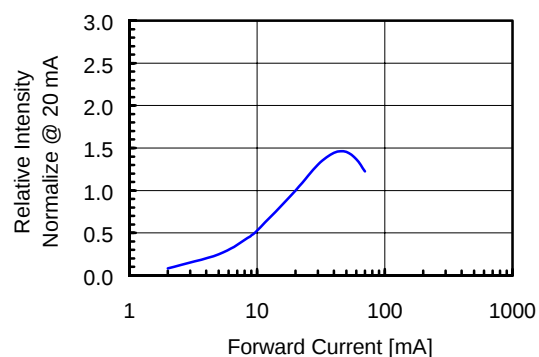


Fig 3. Forward Voltage vs. Temperature

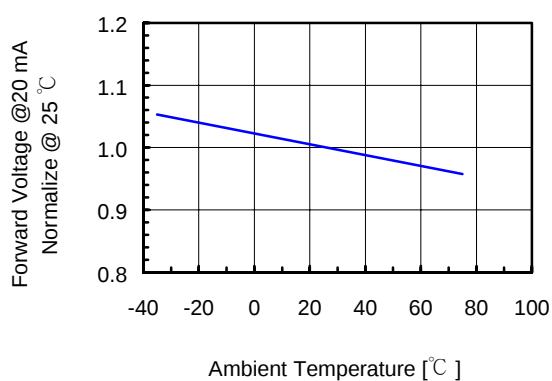


Fig 4. Relative Intensity vs. Temperature

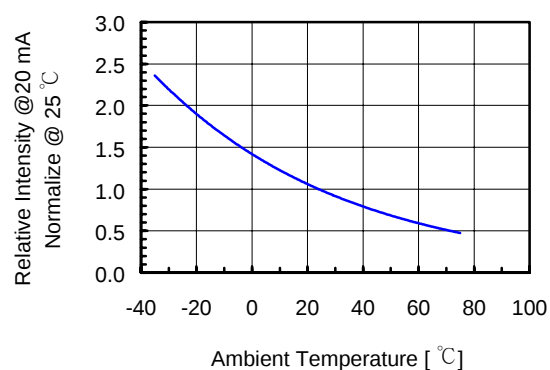
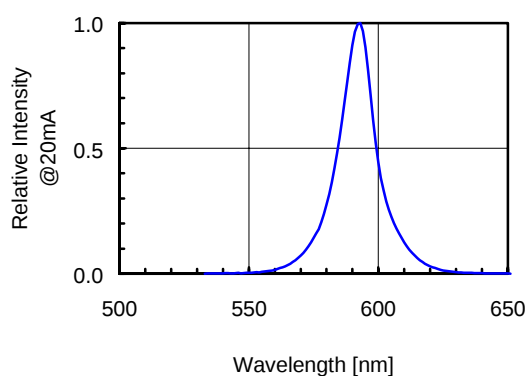


Fig 5. Relative Intensity vs. Wavelength



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